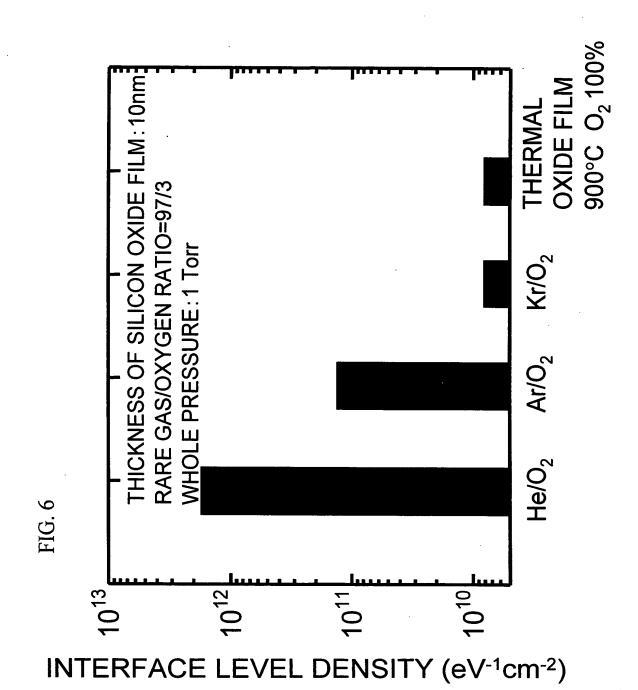
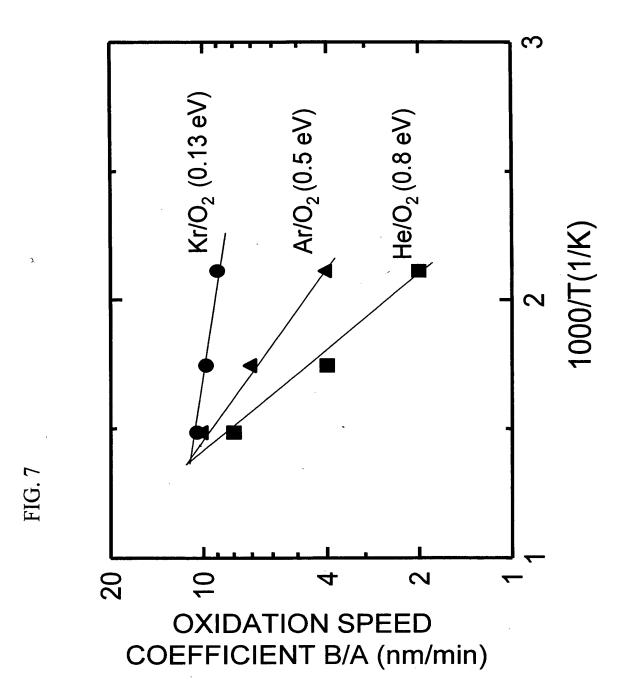
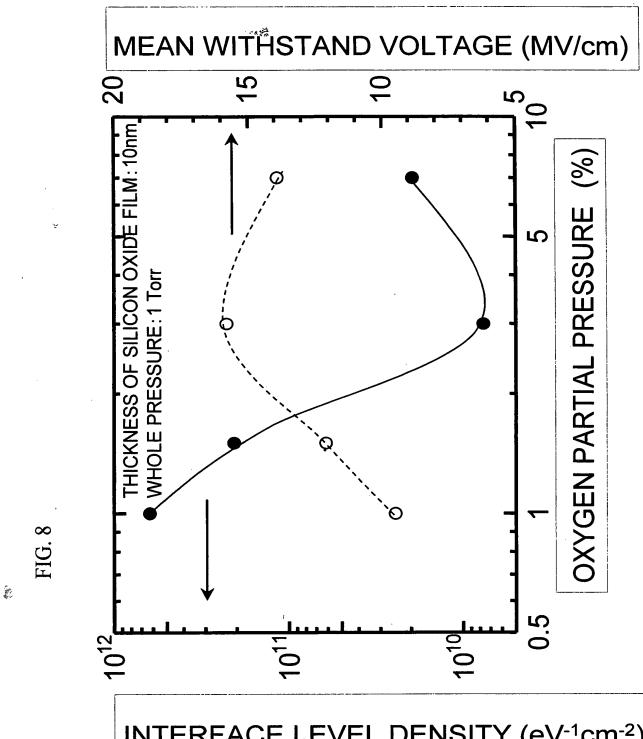


O/Si RATIO IN SILICON OXIDE FILM

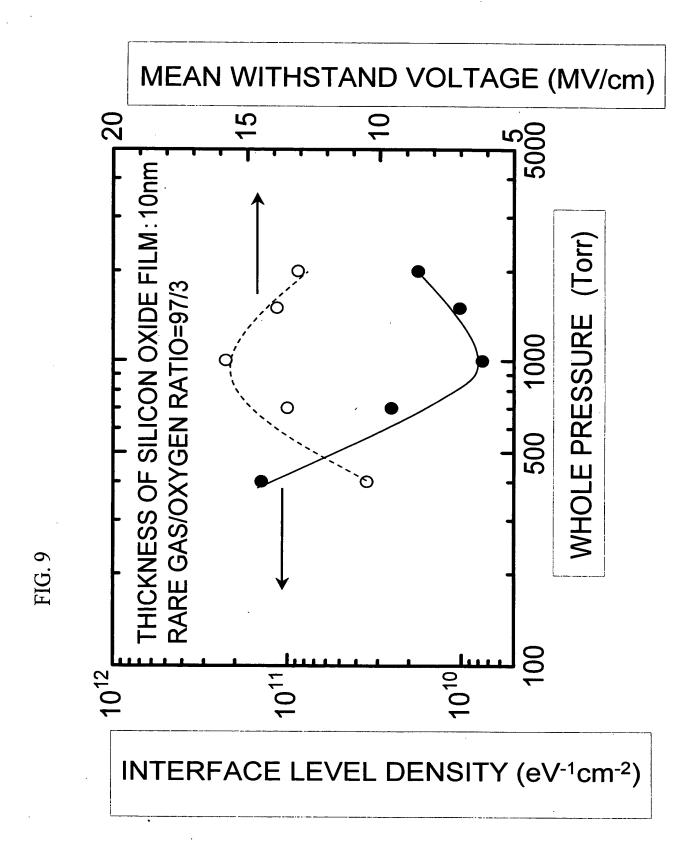


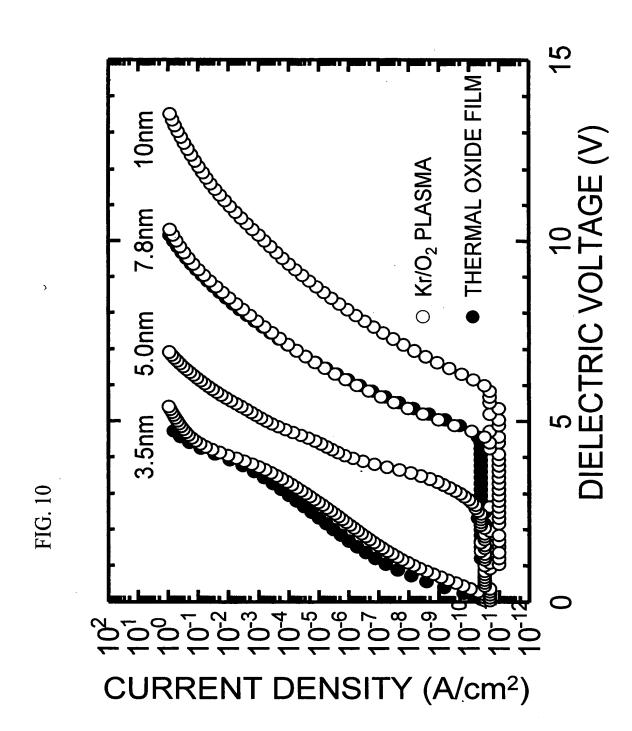


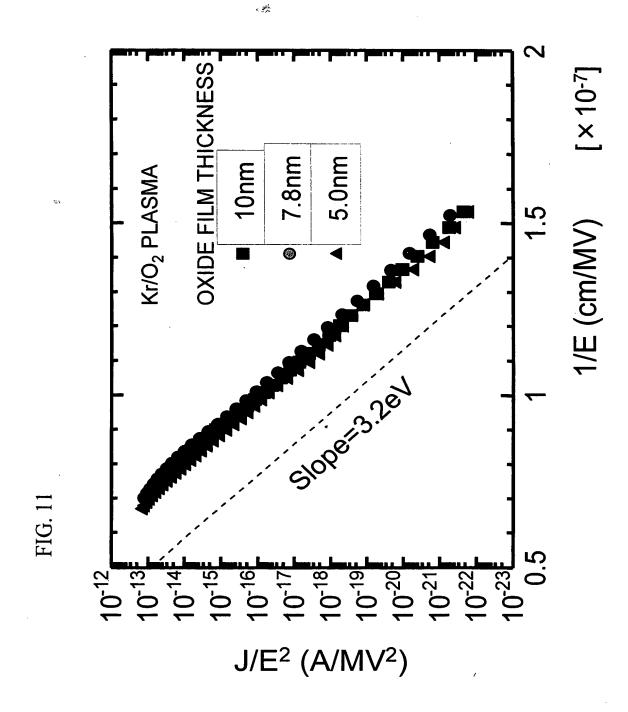
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INTERFACE LEVEL DENSITY (eV-1cm-2)

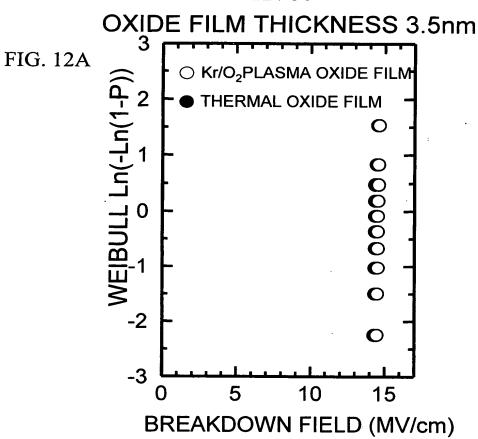




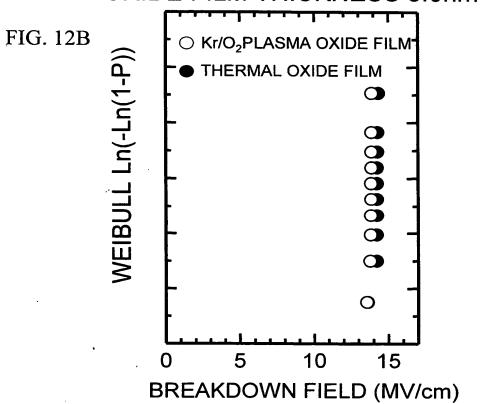


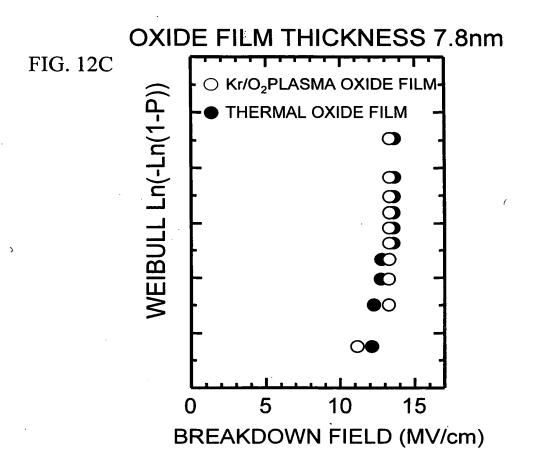
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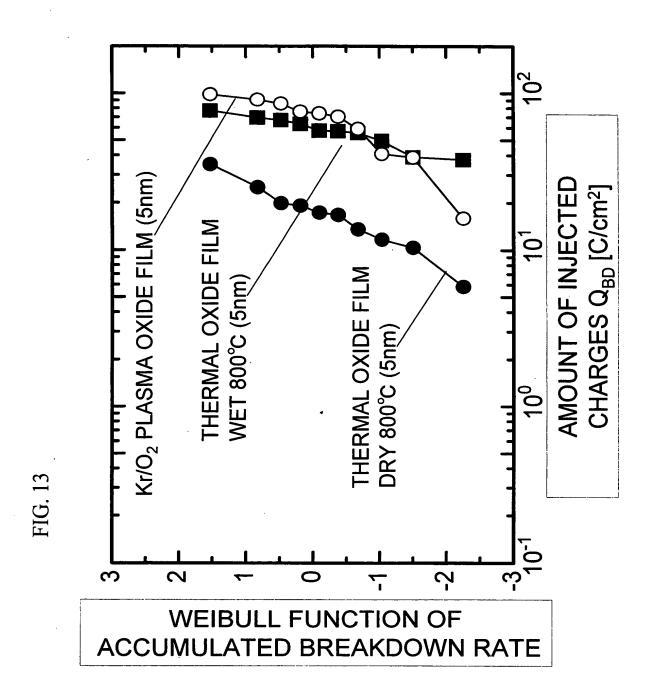


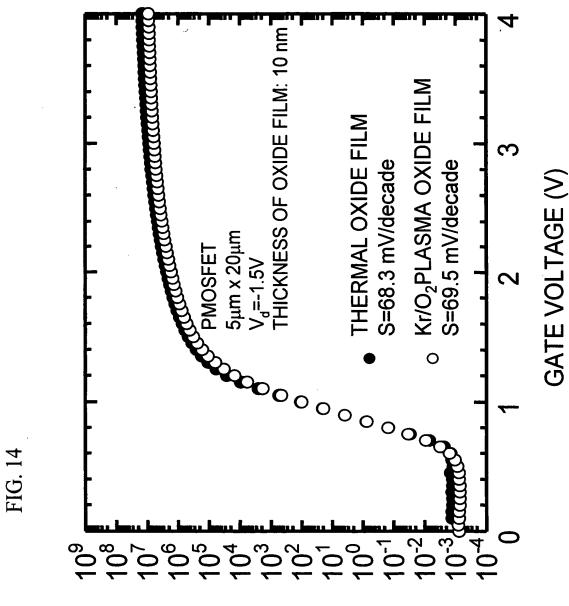




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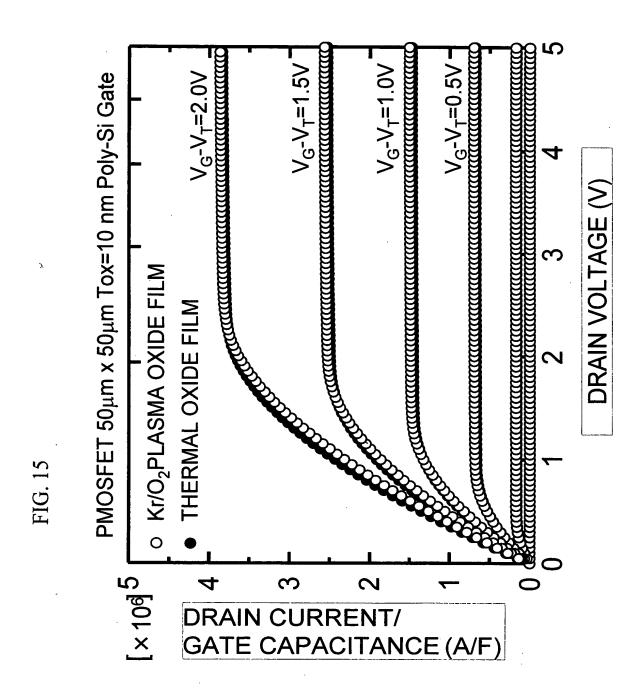
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DRAIN CURRENT/GATE CAPACITANCE (A/F)

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FIG. 16A

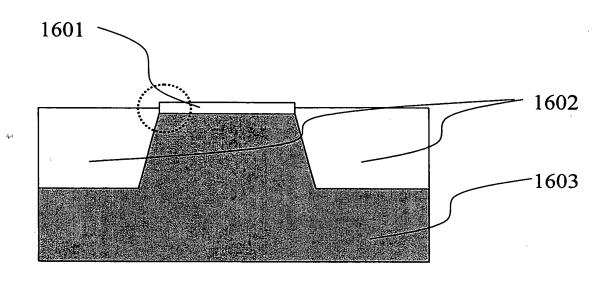
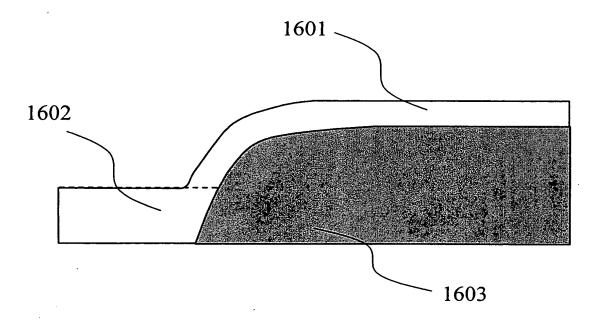
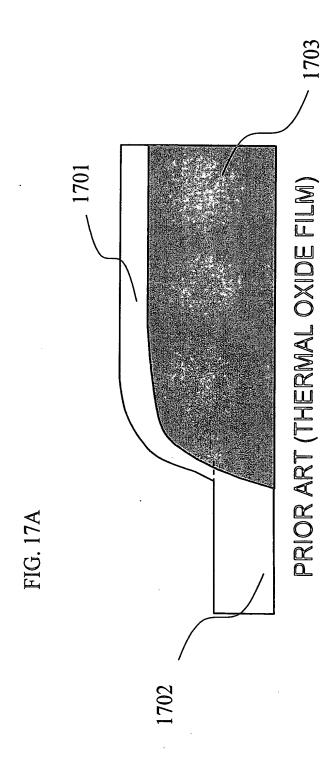
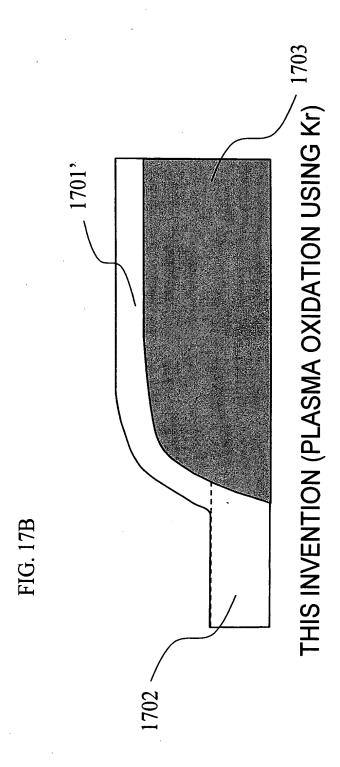


FIG. 16B

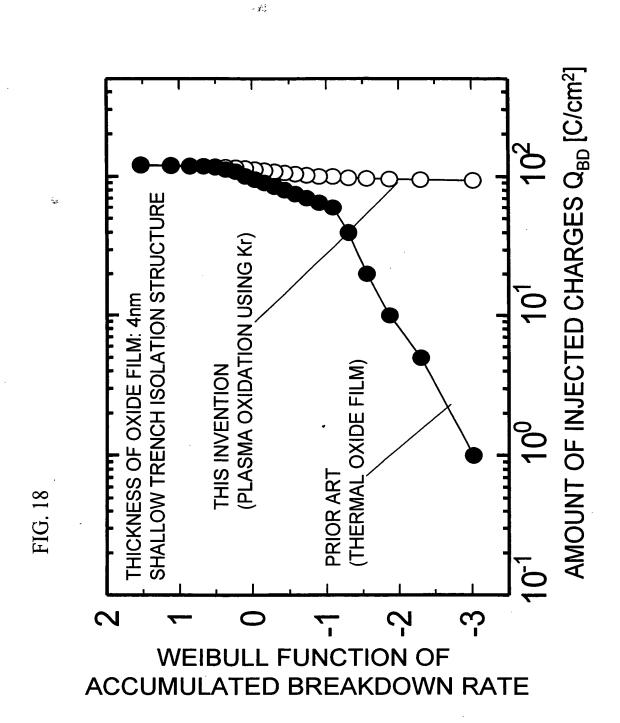


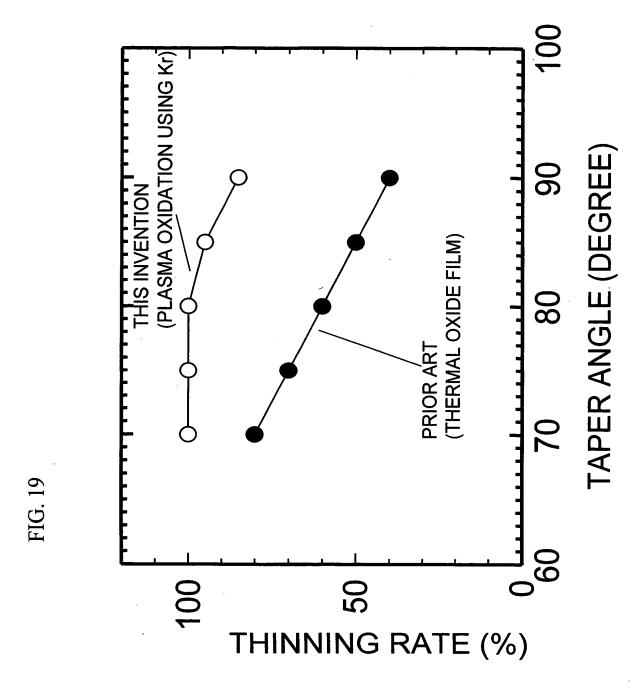


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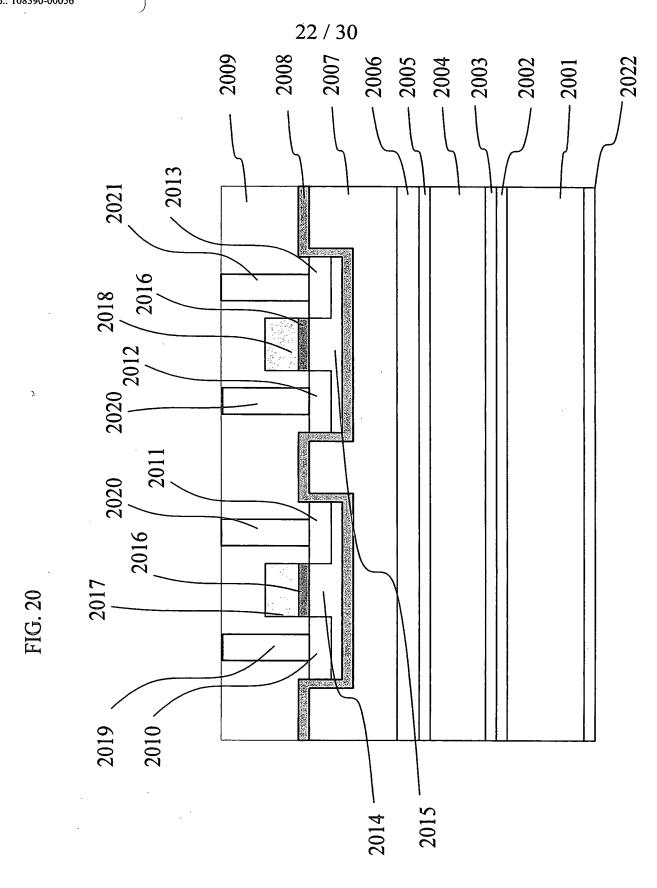


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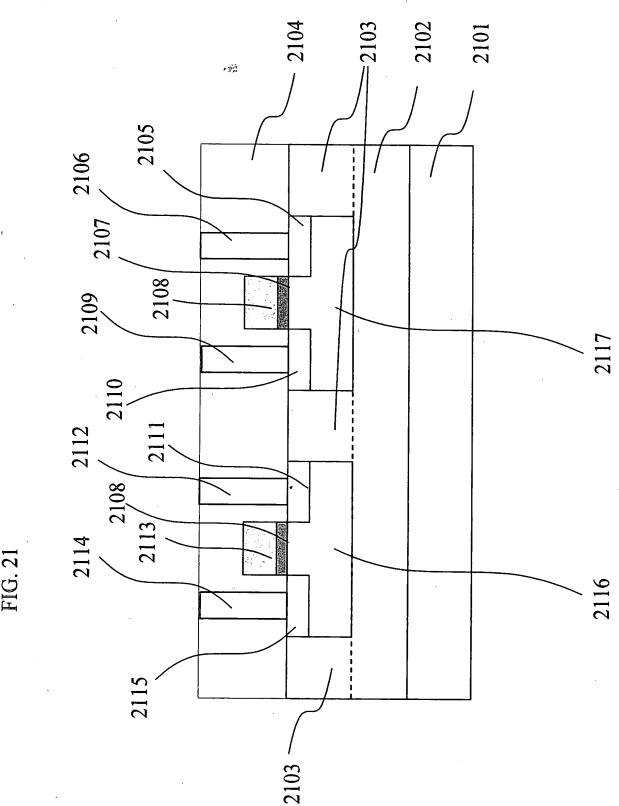


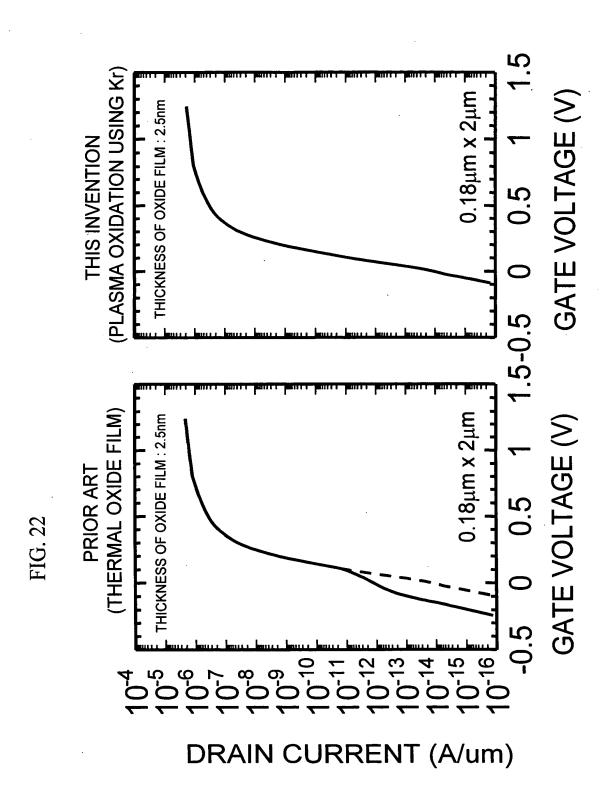
Title: DEVICE HAVING A SILICION OXIDE FILM
CONTAINING KRYPTON
Inventor's Name: Tadahiro OHMI
Divisional of Application No.: 09/787,435
Docket No.: 108390-00056



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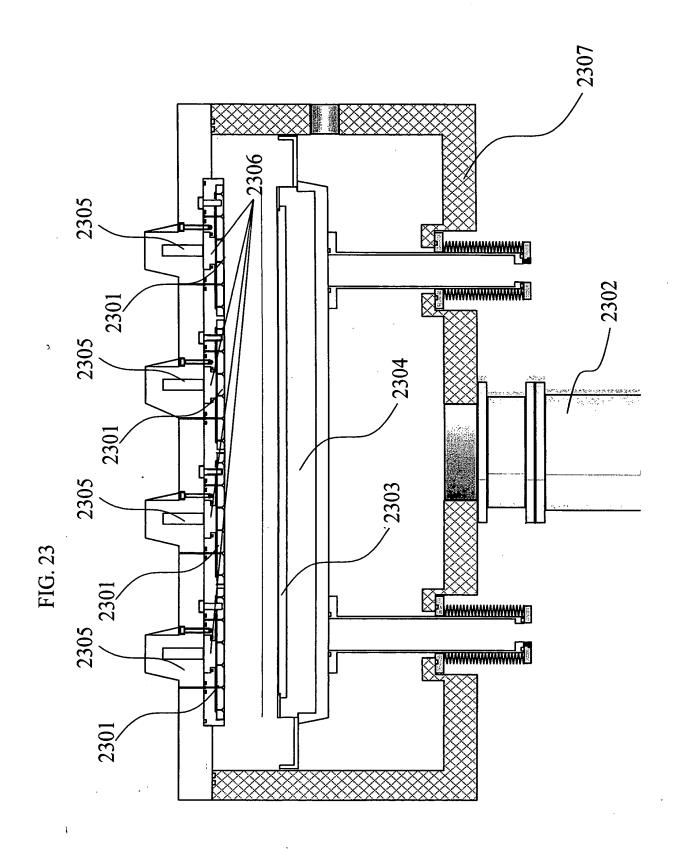


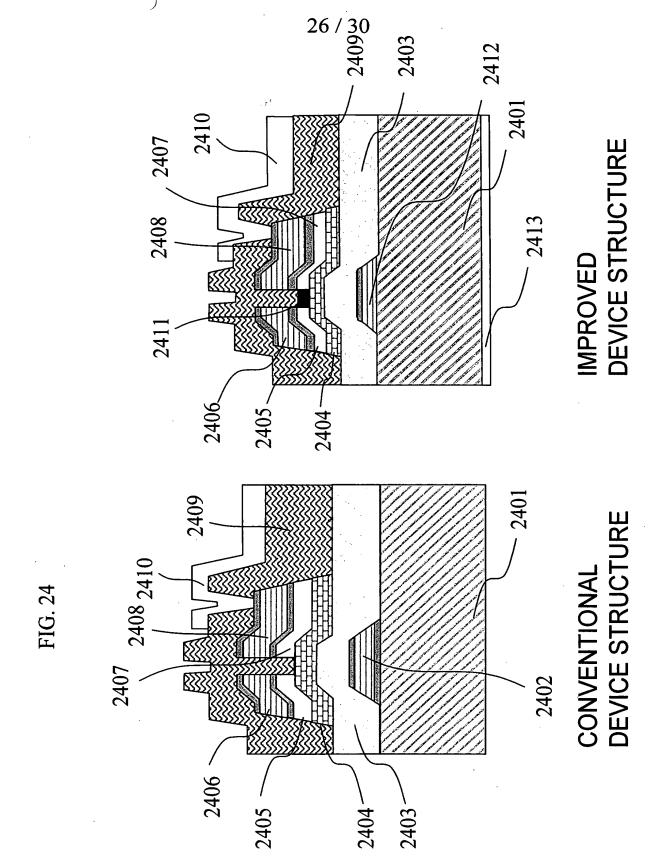


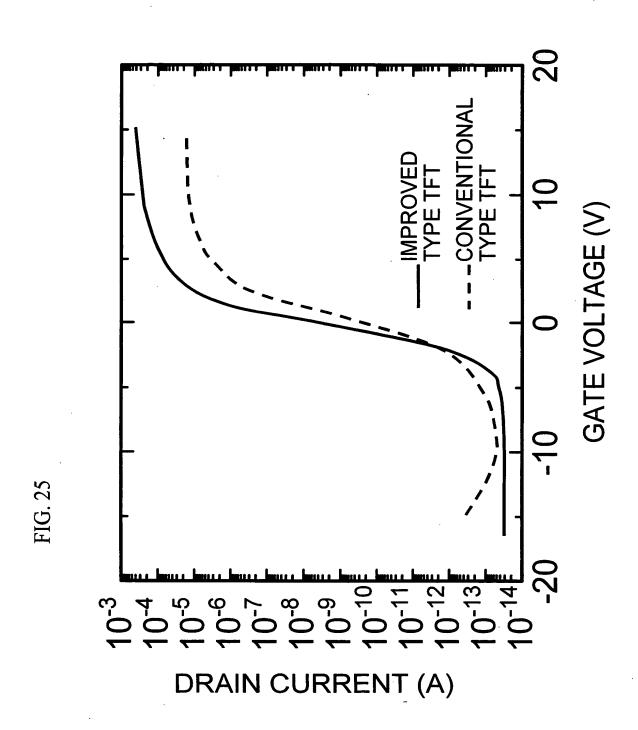


THICKNESS OF OXIDE FILM: 2.5nm

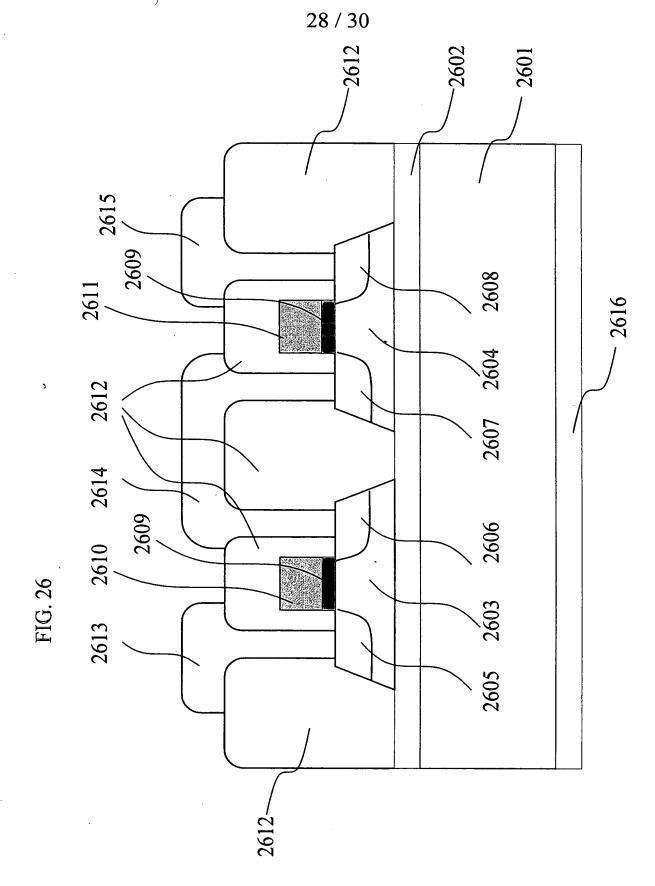
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